

IN THE CLAIMS

Please cancel claims 1, 2 and 7-22 without prejudice or disclaimer.

Fig. 18-27<sup>3</sup>. (Amended, now includes subject matter of claim 1)

A semiconductor device, comprising:

a conductive layer pattern <sup>214a</sup> formed on a substrate;

an inter-layer insulating film <sup>215</sup> which covers said conductive layer pattern and is formed on said substrate;

a first connection hole <sup>216</sup> formed in a upper layer of said inter-layer insulating film above said conductive layer pattern;

a second connection hole <sup>217</sup> which reaches said conductive layer pattern from the bottom portion of said first connection hole and then has a smaller diameter than that of said first connection hole and formed on said inter-layer insulation film; and

a plug <sup>218/218a</sup> having conductivity formed in a state filling internal portions of said first connection hole and said second connection hole;

an upper insulating film <sup>219</sup> formed on said inter-layer insulating film;

a third connection hole <sup>220</sup> which reaches said plug and is formed on said inter-layer insulating film; and

a conductive portion <sup>221</sup> which is connected to said plug and formed in said third connection hole.

4. (Amended, contains subject matter of claims 1 and 2)

A semiconductor device, comprising:

a conductive layer pattern formed on a substrate;

an inter-layer insulating film which covers said conductive layer pattern and is formed on said substrate;

a first connection hole formed in a upper layer of said inter-layer insulating film above said conductive layer pattern;

a second connection hole which reaches said conductive layer pattern from the bottom portion of said first connection hole and then has a smaller diameter than that of said first connection hole and formed on said inter-layer insulation film; and

a plug having conductivity formed in a state filling internal portions of said first connection hole and said second connection hole;

wherein the upper surface of said plug is formed to almost the same height as the surface height of said inter-layer insulating film

an upper insulating film formed on said inter-layer insulating film;

a third connection hole which reaches said plug and is formed on said inter-layer insulating film; and

a conductive contact portion which is connected to said plug and formed in said third connection hole.